

ABSTRACT OF THE DISCLOSURE

A power semiconductor device includes a base layer of first conductivity. A base layer of second conductivity is selectively formed on one surface of the base layer of first conductivity. An emitter layer or source layer of first conductivity is selectively formed on the surface of the base layer of second conductivity. A collector layer or drain layer is selectively formed on the other surface of the base layer of first conductivity or selectively formed on the one surface thereof. A gate electrode is formed on first and second gate insulating films which are formed on part of the base layer of second conductivity which lies between the emitter layer or source layer of first conductivity and the base layer of first conductivity. The capacitance of a capacitor formed of the second gate insulating film is different from that of a capacitor formed of the first gate insulating film.